CLAIMS

1. An Al wiring material comprising an Al core material and an Al coating layer formed on a surface of the Al core material, wherein

the Al wiring material satisfies $1.2 \leq H_{1h}/H_{1s}$

where H_{1s} is a Vickers hardness of the Al core material (Hv) and H_{1h} is a Vickers hardness of the Al coating layer (Hv), and

the Al wiring material satisfies a relation of $x2 < x1$

where x1 is an Al content in the Al core material (mass%) and x2 is an Al content in the Al coating layer (mass%).

2. The Al wiring material according to claim 1, satisfying

$0.5D \leq d_{1sc} \leq 0.95D$

where D is a diameter of the Al wiring material (μm) and d_{1sc} is a diameter of the Al core material (μm).

3. The Al wiring material according to claim 1 or 2, satisfying a relation of $95 \leq x2 < x1$

where x1 is an Al content in the Al core material (mass%) and x2 is an Al content in the Al coating layer (mass%).

4. An Al wiring material comprising an Al core material and an Al coating layer formed on a surface of the Al core material, wherein

the Al wiring material satisfies $1.2 \leq H_{2h}/H_{2s}$

where H_{2h} is a Vickers hardness of the Al core material (Hv) and H_{2s} is a Vickers hardness of the Al

coating layer (Hv), and the Al wiring material satisfies $0.25D \leq d_{2hc} \leq 0.7D$

where D is a diameter of the Al wiring material (μm) and d_{2hc} is a diameter of the Al core material.

5. The Al wiring material according to claim 4, satisfying

$0.3D \leq d_{2hc} \leq 0.65D$

where D is a diameter of the Al wiring material (μm) and d_{2hc} is a diameter of the Al core material.

6. The Al wiring material according to claim 4 or 5, satisfying a relation of $95 \leq y1 < y2$

where y1 is an Al content in the Al core material (mass%) and y2 is an Al content in the Al coating layer (mass%).

7. An Al wiring material according to any one of claims 1 to 3, wherein

the Al coating layer contains 0.2 to 3 mass%, in total, of one or more element selected from the group consisting of Mg, Sc, Y, Ti, Zr, Hf, V, Nb, Cr, Mo, Mn, Fe, Co, Ni, Cu, Ag, Zn and Si (hereinafter, referred to as a "first group element"), and

the Al core material contains 0 to 500 mass ppm, in total, of a metallic element of the group 10 of the periodic table of elements.

8. An Al wiring material according to any one of claims 4 to 6, wherein

the Al core material contains 0.2 to 3 mass%, in total, of one or more element selected from the group

consisting of Mg, Sc, Y, Ti, Zr, Hf, V, Nb, Cr, Mo, Mn, Fe, Co, Ni, Cu, Ag, Zn and Si (hereinafter, referred to as a "first group element"), and

the Al coating layer contains 0 to 500 mass ppm, in total, of a metallic element of the group 10 of the periodic table of elements.

9. The Al wiring material according to claim 7 or 8, wherein the first group element is selected from the group consisting of Sc, Zr, Fe, Ni, Cu and Si.

10. The Al wiring material according to any one of claims 1 to 9, wherein a diameter of the Al wiring material is 100 to 600 μm.

11. The Al wiring material according to any one of claims 1 to 10, wherein the Al wiring material is a bonding wire.

12. A semiconductor device comprising the Al wiring material according to any one of claims 1 to 11.